

Bias Resistor Transistor

NPN Silicon Surface Mount Transistor with Monolithic Bias Resistor Network

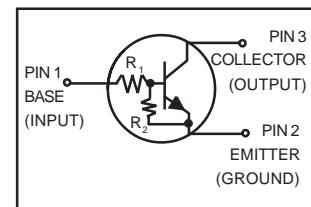
This new series of digital transistors is designed to replace a single device and its external resistor bias network. The BRT (Bias Resistor Transistor) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space. The device is housed in the SC-70/SOT-323 package which is designed for low power surface mount applications.

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- The SC-70/SOT-323 package can be soldered using wave or reflow. The modified gull-winged leads absorb thermal stress during soldering eliminating the possibility of damage to the die.
- Available in 8 mm embossed tape and reel
- Use the Device Number to order the 7 inch/3000 unit reel.
- Pb-Free package is available

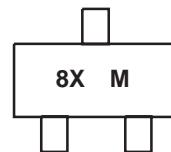
DEVICE MARKING INFORMATION

See specific marking information in the device marking table on page 2 of this data sheet.

**LMUN5211T1G
Series**



MARKINGDIAGRAM



8x = Specific Device Code
x = (See Marking Table)
M= Date Code

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	50	Vdc
Collector-Emitter Voltage	V_{CEO}	50	Vdc
Collector Current	I_C	100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	202 (Note 1.) 310 (Note 2.) 1.6 (Note 1.) 2.5 (Note 2.)	mW $\text{mW}/^\circ\text{C}$
Thermal Resistance – Junction-to-Ambient	$R_{\theta JA}$	618 (Note 1.) 403 (Note 2.)	$^\circ\text{C}/\text{W}$
Thermal Resistance – Junction-to-Lead	$R_{\theta JL}$	280 (Note 1.) 332 (Note 2.)	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

1. FR-4 @ Minimum Pad
2. FR-4 @ 1.0 x 1.0 inch Pad

LMUN5211T1G Series
DEVICE MARKING RESISTOR VALUES AND ORDERING INFORMATION

Device	Package	Marking	R1(K)	R2(K)	Shipping
LMUN5211T1G	SC-70/SOT-323	8A	10	10	3000/Tape&Reel
LMUN5211T3G	SC-70/SOT-323	8A	10	10	10000/Tape&Reel
LMUN5212T1G	SC-70/SOT-323	8B	22	22	3000/Tape&Reel
LMUN5212T3G	SC-70/SOT-323	8B	22	22	10000/Tape&Reel
LMUN5213T1G	SC-70/SOT-323	8C	47	47	3000/Tape&Reel
LMUN5213T3G	SC-70/SOT-323	8C	47	47	10000/Tape&Reel
LMUN5214T1G	SC-70/SOT-323	8D	10	47	3000/Tape&Reel
LMUN5214T3G	SC-70/SOT-323	8D	10	47	10000/Tape&Reel
LMUN5215T1G(Note 3)	SC-70/SOT-323	8E	10	∞	3000/Tape&Reel
LMUN5215T3G	SC-70/SOT-323	8E	10	∞	10000/Tape&Reel
LMUN5216T1G(Note 3)	SC-70/SOT-323	8F	4.7	∞	3000/Tape&Reel
LMUN5216T3G	SC-70/SOT-323	8F	4.7	∞	10000/Tape&Reel
LMUN5230T1G(Note 3)	SC-70/SOT-323	8G	1	1	3000/Tape&Reel
LMUN5230T3G	SC-70/SOT-323	8G	1	1	10000/Tape&Reel
LMUN5231T1G(Note 3)	SC-70/SOT-323	8H	2.2	2.2	3000/Tape&Reel
LMUN5231T3G	SC-70/SOT-323	8H	2.2	2.2	10000/Tape&Reel
LMUN5232T1G(Note 3)	SC-70/SOT-323	8J	4.7	4.7	3000/Tape&Reel
LMUN5232T3G	SC-70/SOT-323	8J	4.7	4.7	10000/Tape&Reel
LMUN5233T1G(Note 3)	SC-70/SOT-323	8K	4.7	47	3000/Tape&Reel
LMUN5233T3G	SC-70/SOT-323	8K	4.7	47	10000/Tape&Reel
LMUN5234T1G(Note 3)	SC-70/SOT-323	8L	22	47	3000/Tape&Reel
LMUN5234T3G	SC-70/SOT-323	8L	22	47	10000/Tape&Reel
LMUN5235T1G(Note 3)	SC-70/SOT-323	8M	2.2	47	3000/Tape&Reel
LMUN5235T3G	SC-70/SOT-323	8M	2.2	47	10000/Tape&Reel
LMUN5236T1G(Note 3)	SC-70/SOT-323	8N	100	100	3000/Tape&Reel
LMUN5236T3G	SC-70/SOT-323	8N	100	100	10000/Tape&Reel
LMUN5237T1G(Note 3)	SC-70/SOT-323	8P	47	22	3000/Tape&Reel
LMUN5237T3G	SC-70/SOT-323	8P	47	22	10000/Tape&Reel

3. New devices. Updated curves to follow in subsequent data sheets.



LMUN5211T1G Series

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector-Base Cutoff Current ($V_{CB} = 50$ V, $I_E = 0$)	I_{CBO}	–	–	100	nAdc
Collector-Emitter Cutoff Current ($V_{CE} = 50$ V, $I_B = 0$)	I_{CEO}	–	–	500	nAdc
Emitter-Base Cutoff Current ($V_{EB} = 6.0$ V, $I_C = 0$)	LMUN5211T1G	I_{EBO}	–	–	0.5
	LMUN5212T1G		–	–	0.2
	LMUN5213T1G		–	–	0.1
	LMUN5214T1G		–	–	0.2
	LMUN5215T1G		–	–	0.9
	LMUN5216T1G		–	–	1.9
	LMUN5230T1G		–	–	4.3
	LMUN5231T1G		–	–	2.3
	LMUN5232T1G		–	–	1.5
	LMUN5233T1G		–	–	0.18
	LMUN5234T1G		–	–	0.13
	LMUN5235T1G		–	–	0.2
	LMUN5236T1G		–	–	0.05
	LMUN5237T1G		–	–	0.13
Collector-Base Breakdown Voltage ($I_C = 10$ μ A, $I_E = 0$)	$V_{(BR)CBO}$	50	–	–	Vdc
Collector-Emitter Breakdown Voltage (Note 4.) ($I_C = 2.0$ mA, $I_B = 0$)	$V_{(BR)CEO}$	50	–	–	Vdc

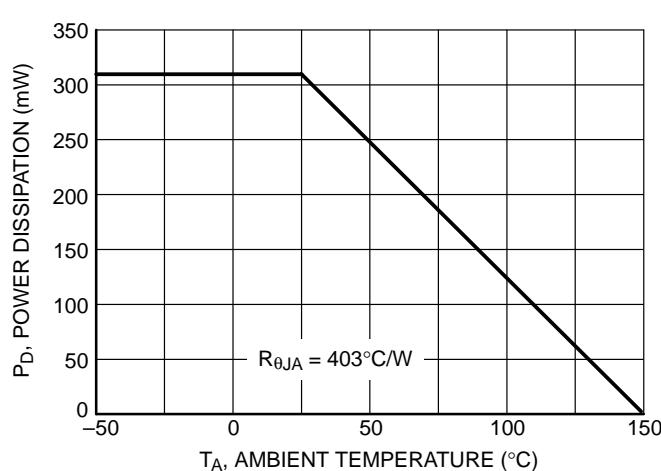
ON CHARACTERISTICS (Note 4.)

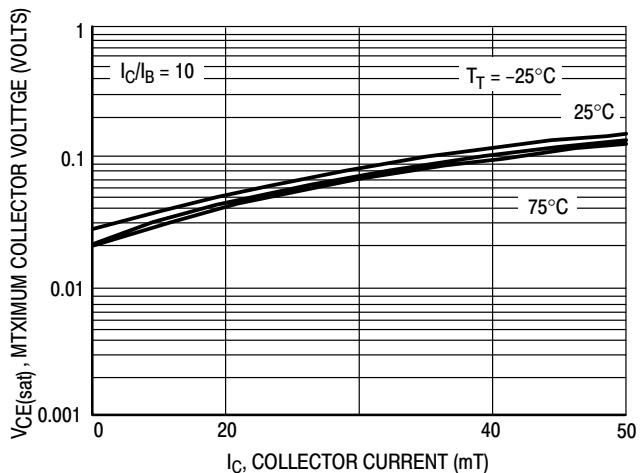
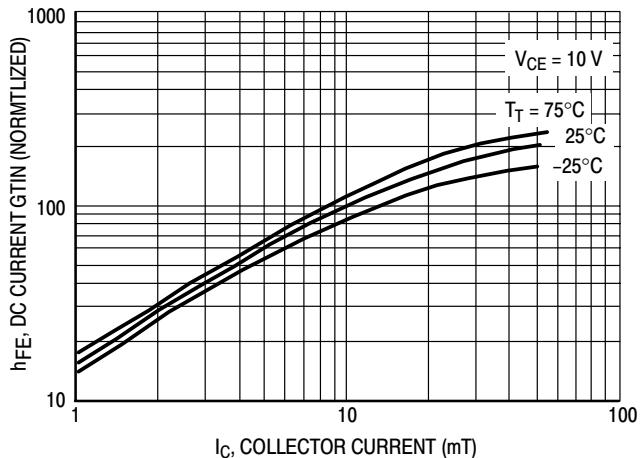
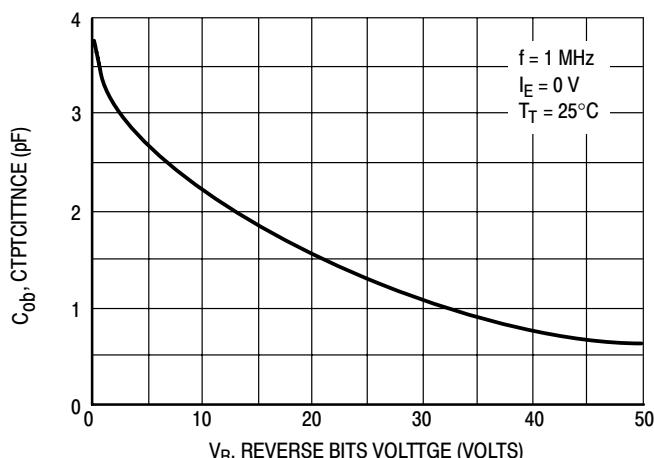
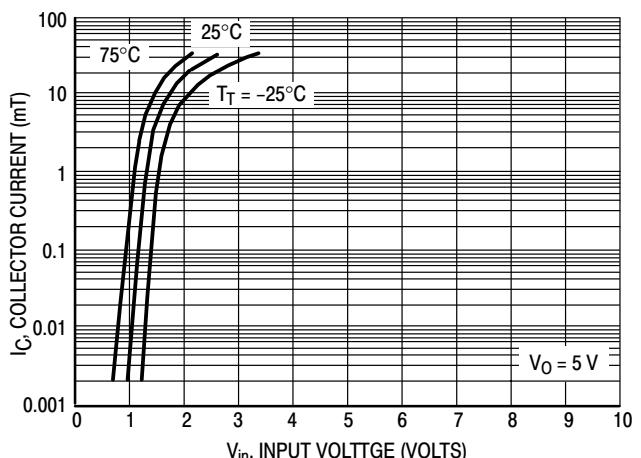
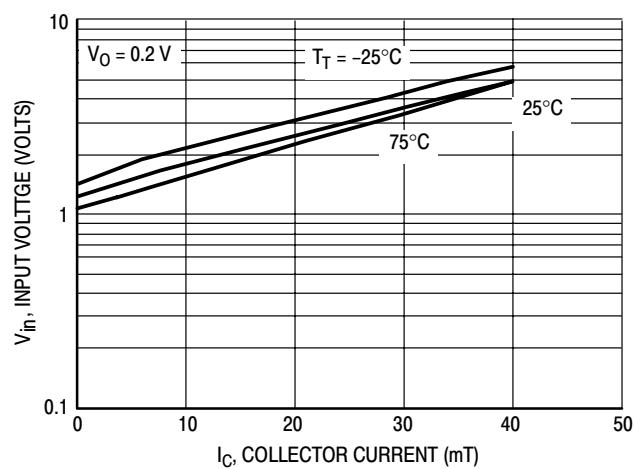
DC Current Gain ($V_{CE} = 10$ V, $I_C = 5.0$ mA)	LMUN5211T1G LMUN5212T1G LMUN5213T1G LMUN5214T1G LMUN5215T1G LMUN5216T1G LMUN5230T1G LMUN5231T1G LMUN5232T1G LMUN5233T1G LMUN5234T1G LMUN5235T1G LMUN5236T1G LMUN5237T1G	h_{FE}	35 60 80 80 160 160 3.0 8.0 15 80 80 80 80 80	60 100 140 140 350 350 5.0 15 30 200 150 140 150 140	— — — — — — — — — — — — — — —	
Collector-Emitter Saturation Voltage ($I_C = 10$ mA, $I_B = 0.3$ mA) ($I_C = 10$ mA, $I_B = 5$ mA) LMUN5230T1/LMUN5231T1 ($I_C = 10$ mA, $I_B = 1$ mA) LMUN5215T1/LMUN5216T1/ LMUN5232T1/LMUN5233T1/LMUN5234T1	$V_{CE(sat)}$	—	—	—	0.25	Vdc
Output Voltage (on) ($V_{CC} = 5.0$ V, $V_B = 2.5$ V, $R_L = 1.0$ k Ω)	LMUN5211T1G LMUN5212T1G LMUN5214T1G LMUN5215T1G LMUN5216T1G LMUN5230T1G LMUN5231T1G LMUN5232T1G LMUN5233T1G LMUN5234T1G LMUN5235T1G	V_{OL}	— — — — — — — — — — —	— — — — — — — — — — —	0.2 0.2 0.2 0.2 0.2 0.2 0.2 0.2 0.2 0.2 0.2	Vdc
($V_{CC} = 5.0$ V, $V_B = 3.5$ V, $R_L = 1.0$ k Ω) ($V_{CC} = 5.0$ V, $V_B = 5.5$ V, $R_L = 1.0$ k Ω) ($V_{CC} = 5.0$ V, $V_B = 4.0$ V, $R_L = 1.0$ k Ω)	LMUN5213T1G LMUN5236T1G LMUN5237T1G	— — —	— — —	— — —	0.2 0.2 0.2	

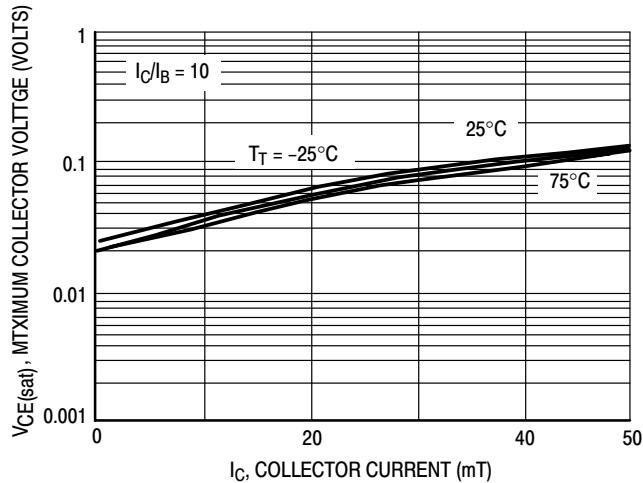
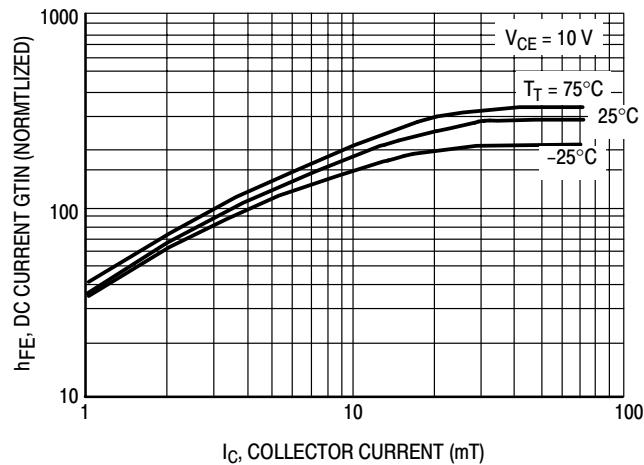
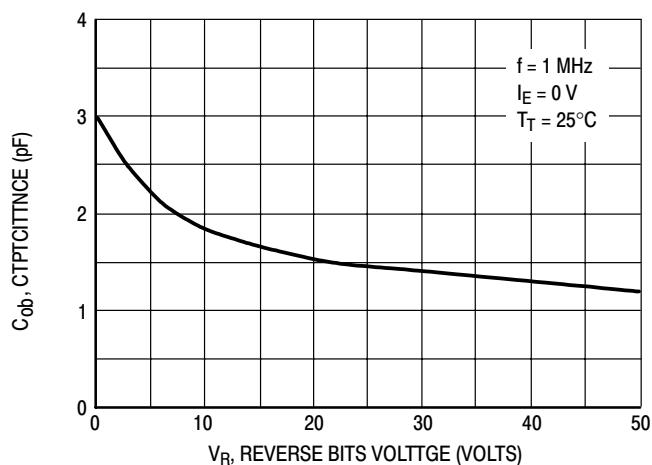
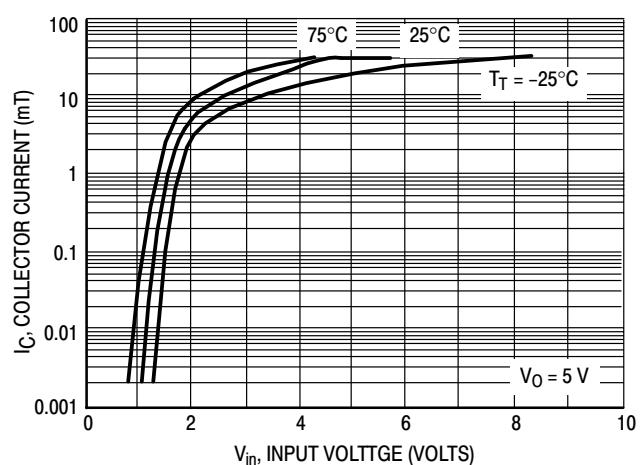
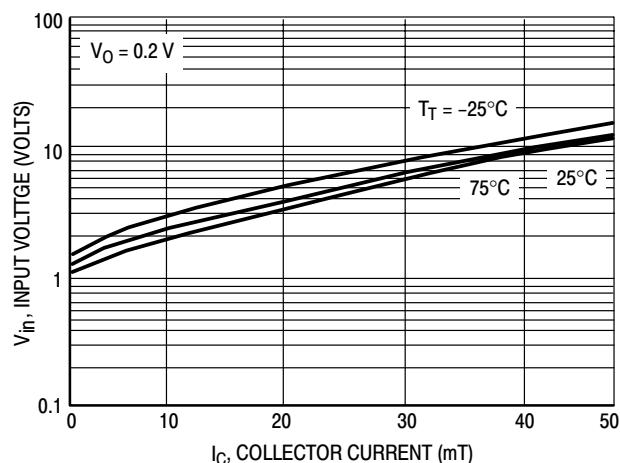
4. Pulse Test: Pulse Width < 300 μs, Duty Cycle < 2.0%

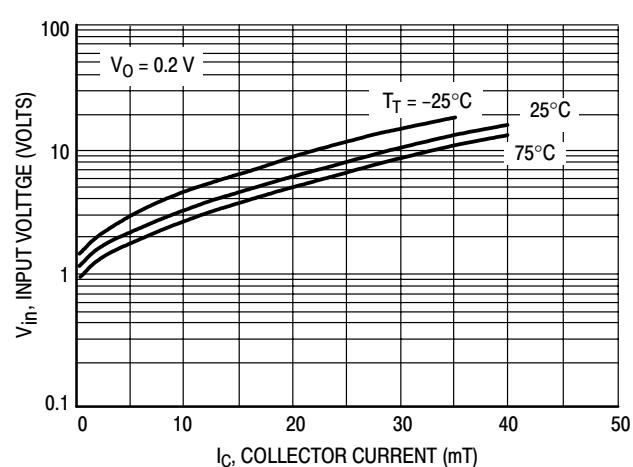
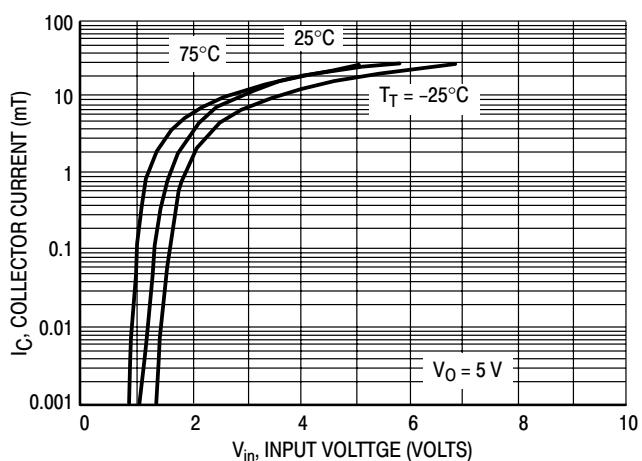
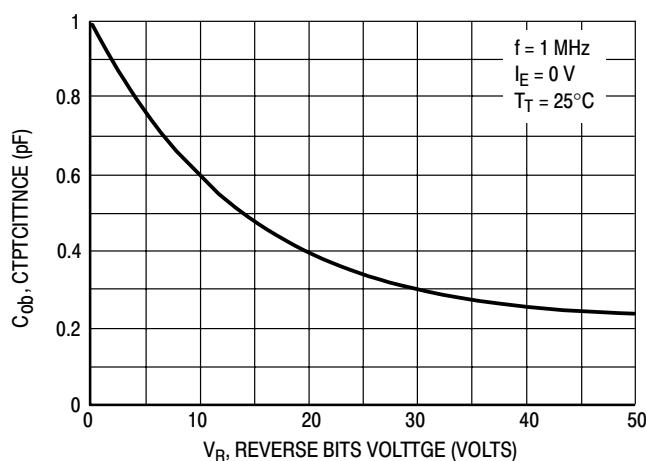
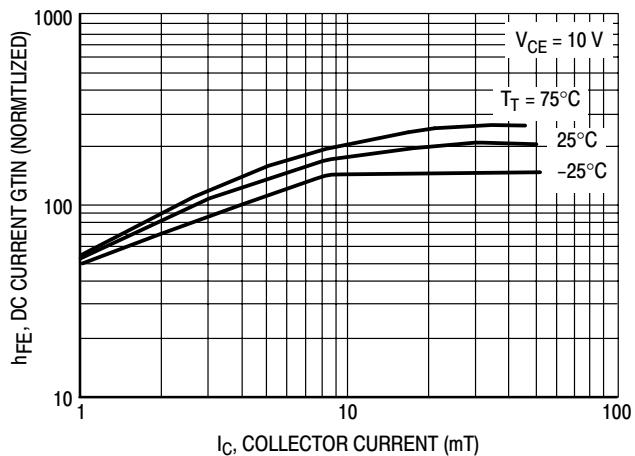
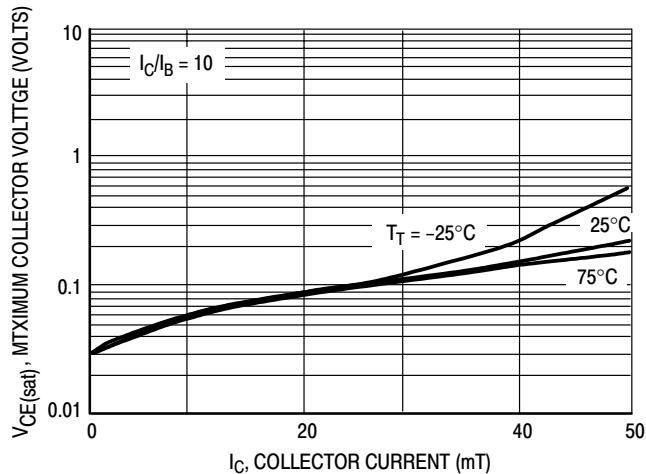
LMUN5211T1G Series
ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS (Note 5.) (Continued)					
Output Voltage (off) ($V_{CC} = 5.0 \text{ V}$, $V_B = 0.5 \text{ V}$, $R_L = 1.0 \text{ k}\Omega$) ($V_{CC} = 5.0 \text{ V}$, $V_B = 0.050 \text{ V}$, $R_L = 1.0 \text{ k}\Omega$) ($V_{CC} = 5.0 \text{ V}$, $V_B = 0.25 \text{ V}$, $R_L = 1.0 \text{ k}\Omega$)	V_{OH}	4.9	—	—	Vdc
Input Resistor	R_1	7.0 15.4 32.9 7.0 7.0 3.3 0.7 1.5 3.3 3.3 15.4 1.54 70 32.9	10 22 47 10 10 4.7 1.0 2.2 4.7 4.7 22 2.2 100 47	13 28.6 61.1 13 13 6.1 1.3 2.9 6.1 6.1 28.6 2.86 130 61.1	kΩ
Resistor Ratio	R_1/R_2	0.8 0.17 — 0.8 0.055 0.38 0.038 1.7	1.0 0.21 — 1.0 0.1 0.47 0.047 2.1	1.2 0.25 — 1.2 0.185 0.56 0.056 2.6	
5. Pulse Test: Pulse Width < 300 μs, Duty Cycle < 2.0%					


Figure 1. Derating Curve

LMUN5211T1G Series
TYPICAL ELECTRICAL CHARACTERISTICS – LMUN5211T1G

Figure 2. $V_{CE(\text{sat})}$ versus I_C

Figure 3. DC Current Gain

Figure 4. Output Capacitance

Figure 5. Output Current versus Input Voltage

Figure 6. Input Voltage versus Output Current

LMUN5211T1G Series
TYPICAL ELECTRICAL CHARACTERISTICS – LMUN5212T1G

Figure 7. $V_{CE(sat)}$ versus I_C

Figure 8. DC Current Gain

Figure 9. Output Capacitance

Figure 10. Output Current versus Input Voltage

Figure 11. Input Voltage versus Output Current

LMUN5211T1G Series
TYPICAL ELECTRICAL CHARACTERISTICS – LMUN5213T1G


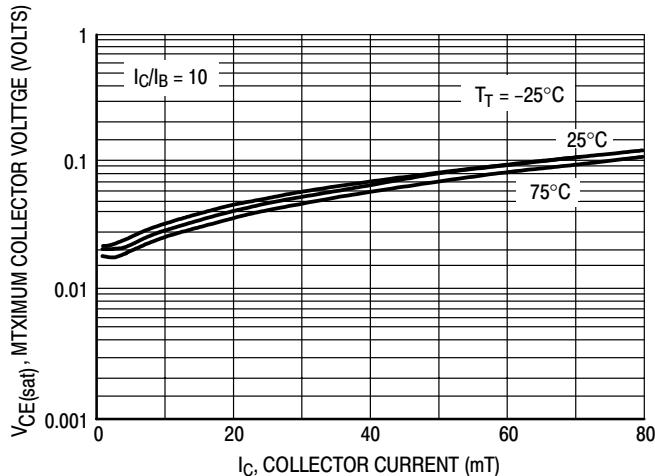
LMUN5211T1G Series
TYPICAL ELECTRICAL CHARACTERISTICS – LMUN5214T1G


Figure 17. $V_{CE(sat)}$ versus I_C

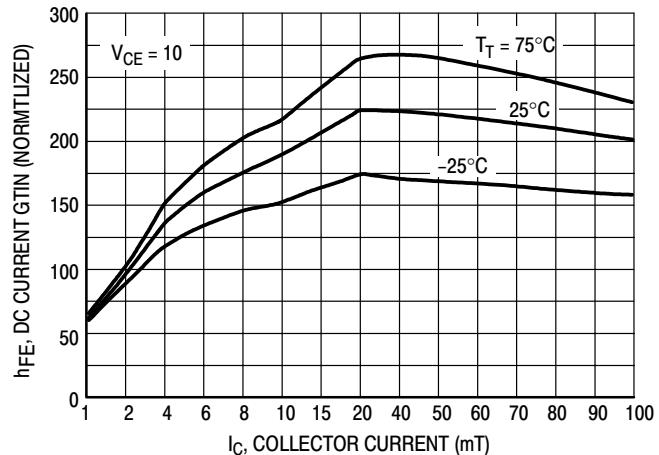


Figure 18. DC Current Gain

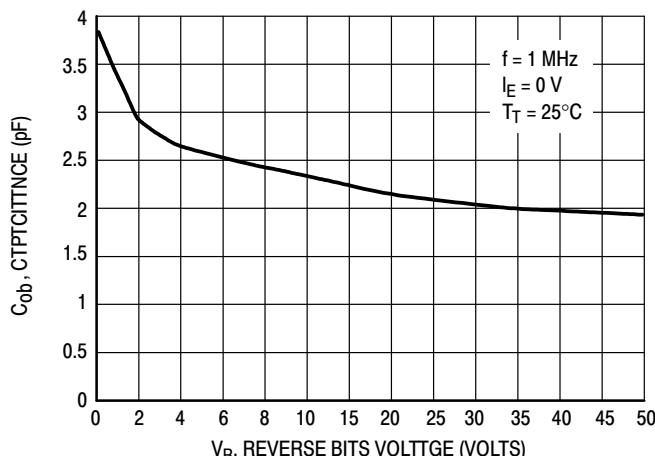


Figure 19. Output Capacitance

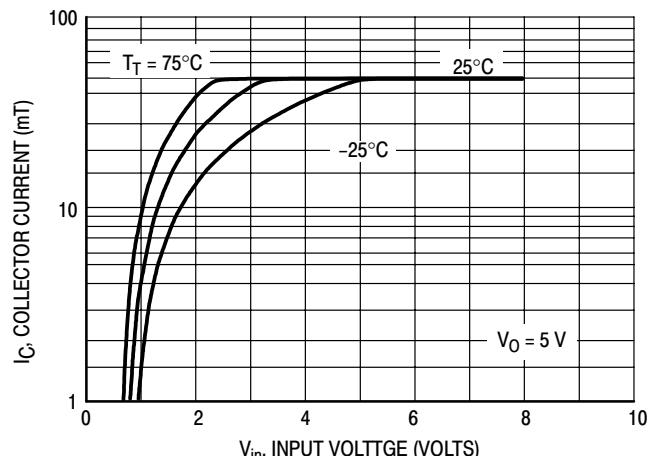


Figure 20. Output Current versus Input Voltage

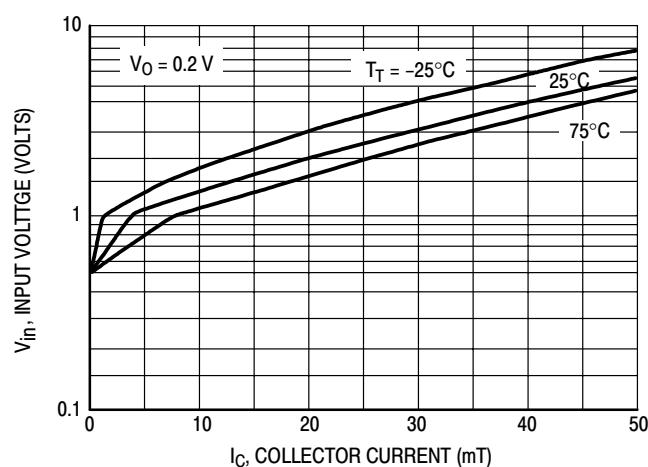


Figure 21. Input Voltage versus Output Current

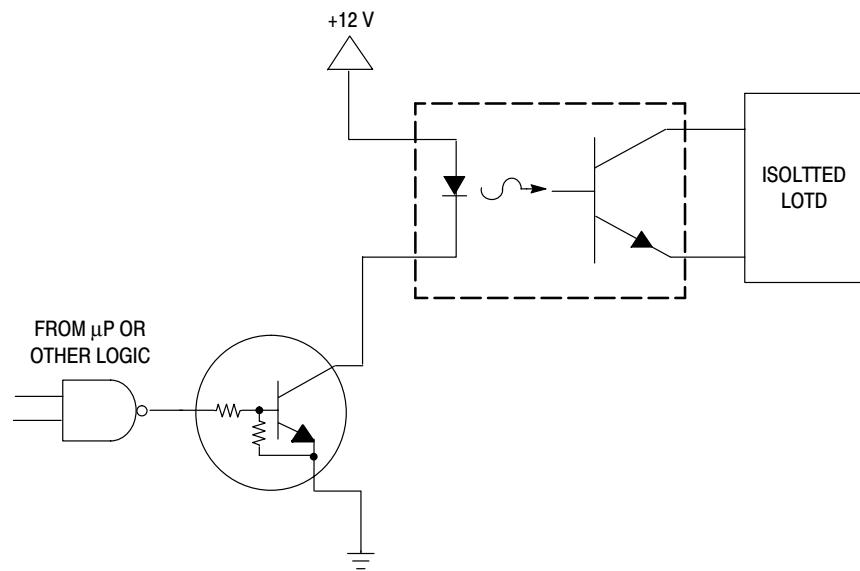
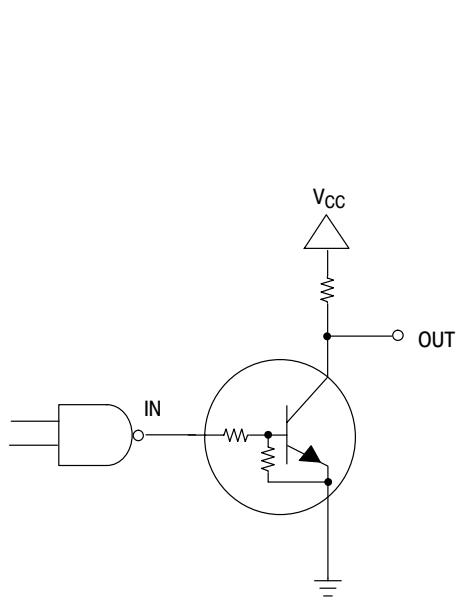
LMUN5211T1G Series
TYPICAL APPLICATIONS FOR NPN BRTs


Figure 22. Level Shifter: Connects 12 or 24 Volt Circuits to Logic



**Figure 23. Open Collector Inverter:
Inverts the Input Signal**

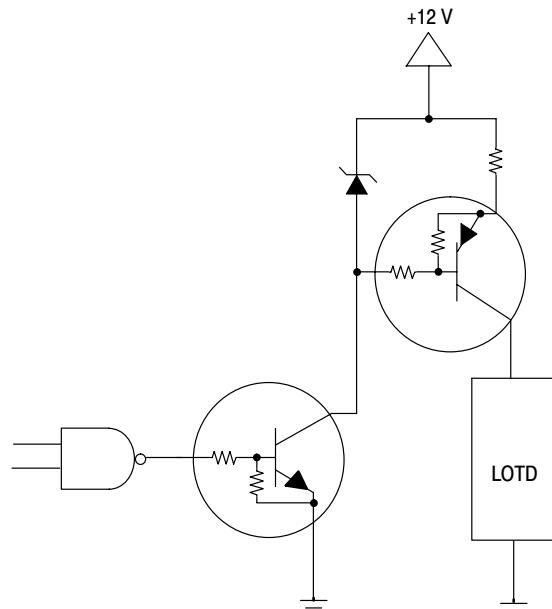
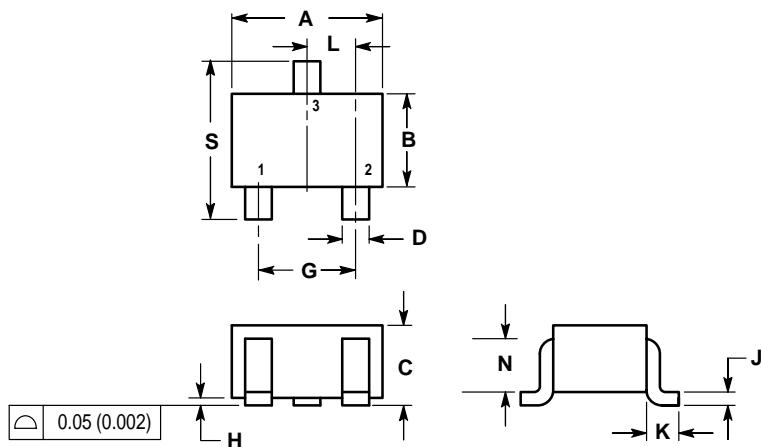


Figure 24. Inexpensive, Unregulated Current Source

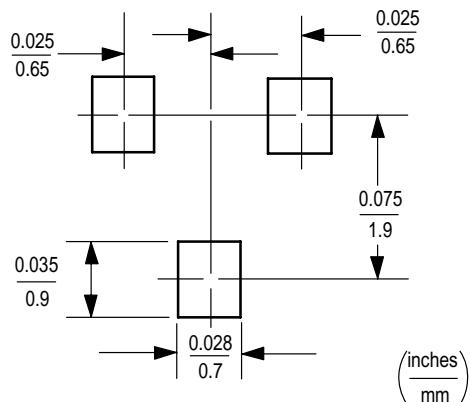
LMUN5211T1G Series
SC-70 / SOT-323
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.032	0.040	0.80	1.00
D	0.012	0.016	0.30	0.40
G	0.047	0.055	1.20	1.40
H	0.000	0.004	0.00	0.10
J	0.004	0.010	0.10	0.25
K	0.017	REF	0.425	REF
L	0.026	BSC	0.650	BSC
N	0.028	REF	0.700	REF
S	0.079	0.095	2.00	2.40

PIN 1. BASE
2. Emitter
3. Collector



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